

ABSTRACT

There is provided a technique that includes: (a) forming a silicon seed layer on a substrate by performing a cycle a predetermined number of times, the cycle including non-simultaneously performing: (a1) supplying a first gas containing halogen and silicon to the substrate; and (a2) supplying a second gas containing hydrogen to the substrate; and (b) forming a film containing silicon on the silicon seed layer by supplying a third gas containing silicon to the substrate, wherein a pressure of a space in which the substrate is located in (a2) is set higher than a pressure of the space in which the substrate is located in (a1).

FIG. 4